

Abstract

A method of patterning a transparent conductive film adaptive for selectively etching a transparent conductive film without any mask processes, a thin film transistor for a display device using the same and a fabricating method thereof are disclosed. In the method of patterning the transparent conductive film, an inorganic material substrate is prepared. An organic material pattern is formed at a desired area of the inorganic material substrate. A thin film having a different crystallization rate depending upon said inorganic material and said organic material is formed. The thin film is selectively etched in accordance with said crystallization rate.